BUK7K25-40E

Dual N-channel TrenchMOS standard level FET

23 April 2013

Product data sheet

1. General description

Dual standard level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} > 1 V @ 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V	
I _D	drain current	V _{GS} = 10 V; Tmb = 25 °C; <u>Fig. 1</u>		-	-	27	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	32	W	
Static characte	Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 12$		-	21.25	25	mΩ	
Dynamic characteristics FET1 and FET2								
Q_{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14; Fig. 15$		-	2.6	-	nC	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
3	S2	source2		
4	G2	gate2		
5	D2	drain2	S1 G1	
6	D2	drain2	O O O	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	2	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7K25-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K25-40E	72540E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ; $T_j \ge 25$ °C; $T_j \le 175$ °C	-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	V _{GS} = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	-	27	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	19	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4	-	107	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	32	W

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drai	in diode FET1 and FET2			'		
Is	source current	T _{mb} = 25 °C		-	27	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	107	Α
Avalanche l	Ruggedness FET1 and FET2		1	'		
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 28 \text{ A; } V_{sup} \le 40 \text{ V; } V_{GS} = 10 \text{ V;}$ $T_{j(init)} = 25 \text{ °C; } Fig. 3$	[1][2]	-	10	mJ

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

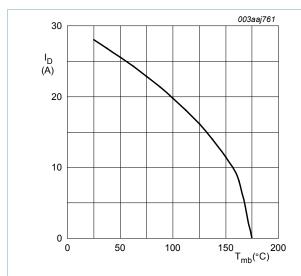


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10 V$$

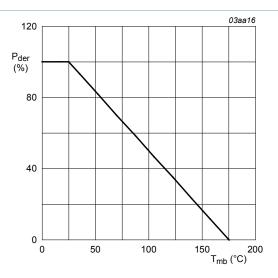


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$

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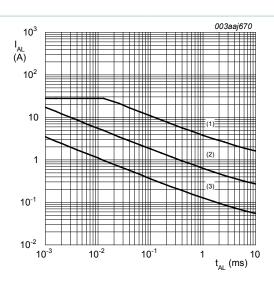


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse; $T_j = 25 \,^{\circ}C$.
- (2) Single-pulse; $T_j = 150 \,^{\circ}C$.
 - (3) Repetitive.

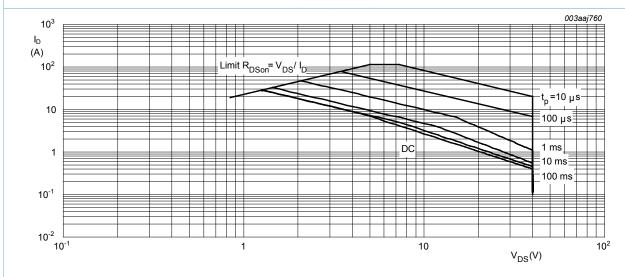


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$$T_{mb} = 25 \,^{\circ}C$$
; I_{DM} is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	4.68	K/W

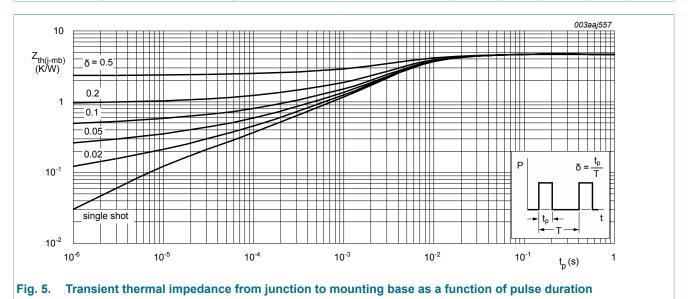
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mi	in	Тур	Max	Unit
Static chara	acteristics FET1 and FET2						
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	3	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40)	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2.	4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	1		-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-		-	4.5	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-		-	500	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-		0.02	1	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-		2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-		2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-		21.25	25	mΩ
	resistance	V_{GS} = 10 V; I_D = 5 A; T_j = 175 °C; Fig. 12; Fig. 13	-		40.1	49.3	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics FET1 and FE	T2	·			
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	7.9	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14; Fig. 15</u>	-	1.5	-	nC
Q_{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 32 V; V _{GS} = 20 V; T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.6	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	394	525	pF
C _{oss}	output capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 16</u>	-	107	128	pF
C _{rss}	reverse transfer capacitance		-	76	104	pF
t _{d(on)}	turn-on delay time	V_{DS} = 32 V; R_{L} = 6.5 Ω ; V_{GS} = 10 V;	-	4.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$	-	4.5	-	ns
t _{d(off)}	turn-off delay time		-	8.3	-	ns
t _f	fall time		-	5.2	-	ns
Source-dra	in diode FET1 and FET2	1				
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	12.4	-	ns
Q _r	recovered charge	V _{DS} = 20 V; T _j = 25 °C	-	6.7	-	nC

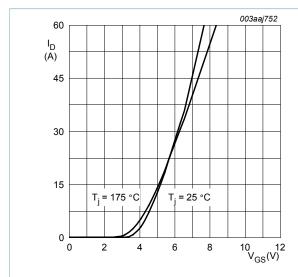


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$

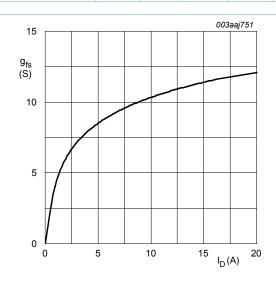


Fig. 7. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$$

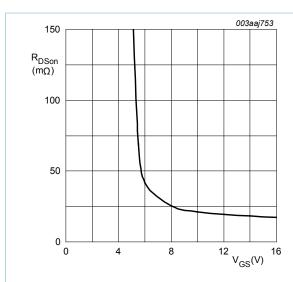


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



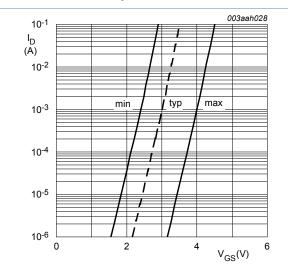


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

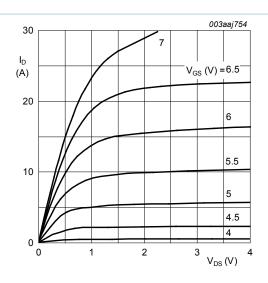


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

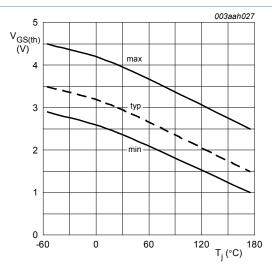


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

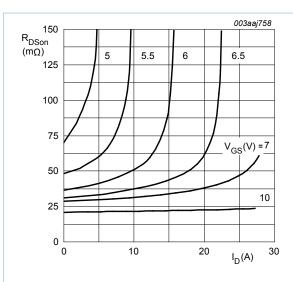


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

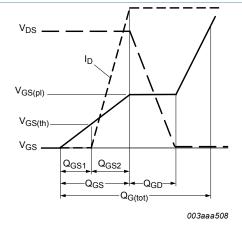


Fig. 14. Gate charge waveform definitions

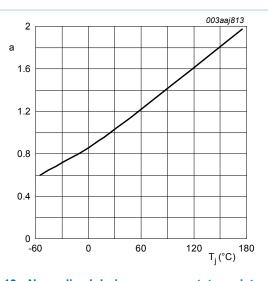


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

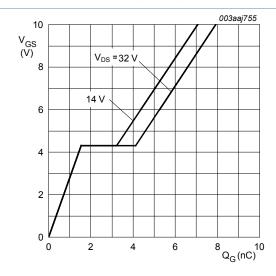


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 5A$$

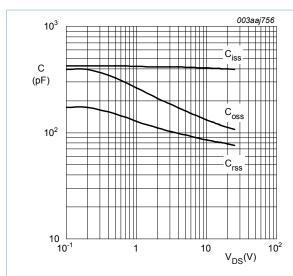
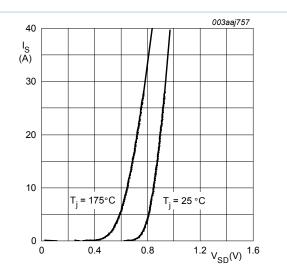


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values

$$V_{GS} = 0 V; f = 1MHz$$

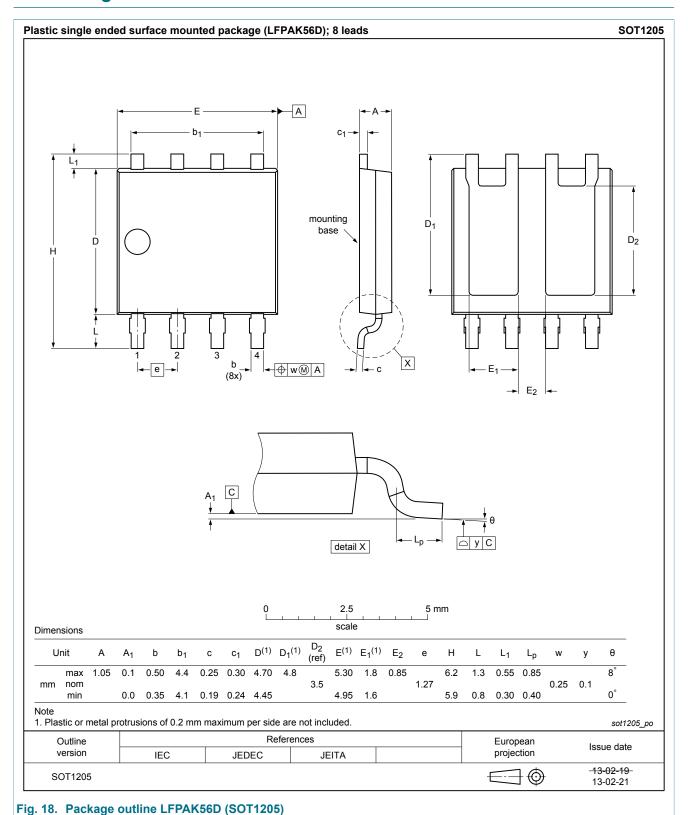


voltage; typical values

$$V_{GS} = 0 V$$

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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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